

21 2. (Amended) ~~The method of claim 1 further comprising forming circuitry in the second region of the substrate outside the first region.~~

3. The method of claim 2 further comprising depositing an electrical connection over the first trench to connect the microstructure to the circuitry.

4. ¹² The method of claim 1 further comprising depositing a filler material over the isolation layer in the first trench. }

5. The method of claim 1 wherein the isolation layer fills the first trench. }

6. The method of claim 1 wherein the substrate further includes a handle layer and a sacrificial layer. }

7. The method of claim 6 wherein the method further comprises removing a portion of the sacrificial layer to release the microstructure. ✓

8. The method of claim 7 wherein the step of etching the first trench etches through the device layer to expose the sacrificial layer.

9. The method of claim 7 wherein the step of etching the second trench etches through the device layer to expose the sacrificial layer.

10. The method of claim 6 wherein the sacrificial layer includes silicon dioxide.

11. The method of claim 1 wherein the device layer includes epitaxial silicon.

12. The method of claim 1 wherein the isolation layer includes silicon nitride.)